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Table of Contents

Neutron-Induced SEEs in the Xilinx Versai Prime	1
<i>Heather Quinn, Los Alamos National Laboratory, ISR-3 Space Data Systems, Los Alamos, NM, 87545 USA; Charles Corley, Department of Electrical & Computer Engineering, University of Texas at Austin; and Paul Thelen, Sandia National Laboratories, Albuquerque</i>	
Proton Induced Single Event Effects on the Arria 10 Commercial Off-the-Shelf CMOS Field Programmable Gate Array	9
<i>R. Koga, S. Davis, A. Yarbrough, J. Shanney, Kenneth Pham, C. Cao, Kevin Pham, and J. Dixon, The Aerospace Corporation, El Segundo, CA 90245</i>	
64MeV Proton Single-Event Evaluation of Xilinx Single Event Mitigation (XilSEM) Firmware on 7nm Versal™ ACAP Devices	14
<i>Yanran Paula Chen, Pierre Maillard, Rama Devi Veggalam, Saraschandra Reddy Madem, Eric Crabill, Jeff Barton, and Martin Voogel</i>	
Neutron and 64MeV Proton Characterization of Xilinx 7nm Versal™ Multicore Scalar Processing System (PS)	18
<i>Pierre Maillard, Y. Paula Chen, Jue Arver, Venkatesh Merugu, Ava Shui, and Martin Voogel</i>	
Compendium of Current Heavy Ion Single-Event Effects Test Results for Candidate Electronics for NASA Johnson Space Center	23
<i>Joshua M. Pritts, Razvan Gaza, Charles R. Bailey, and Kyson V. Nguyen, The NASA Johnson Space Center, EV5 Electronic Design and Manufacturing Branch, 2101 NASA Parkway</i>	
Extended Compendium of Total Ionizing Dose (TID) Test Results for the Europa Clipper Mission	28
<i>Stephanie Zajac, Amanda Bozovich, Stacie Woo, NASA Jet Propulsion Laboratory, California Institute of Technology, 4800 Oak Grove Drive; Rob Davies, University of St. Thomas, St Paul; Bernie Rax, Joe Davila, NASA Jet Propulsion Laboratory, California Institute of Technology, 4800 Oak Grove Drive; Duc Nguyen, Northrop Grumman Corporation, Redondo Beach; Wilson Parker, Aaron Kenna, and Jason Thomas, NASA Jet Propulsion Laboratory, California Institute of Technology, 4800 Oak Grove Drive</i>	
A Study of Neutron Induced Single-Event Damage in AlGaN/GaN HEMTs	42
<i>Han Gao, Danyal Ahsanullah, Robert Baumann, and Bruce Gnade</i>	
100SW1502 Optocoupler TID & DDD Tests	48
<i>Zachary D. Olson, Roberto Monreal, and Jonathan Vloet</i>	
Characterization of the Effects of 250 MeV Proton-Induced Total Ionizing Dose and Displacement Damage on the 66266 Optocoupler	53
<i>Scott Messenger, Codie Mishler, James Hack, and Paul Dudek, Northrop Grumman Corporation, Linthicum Heights</i>	
Single Event Effects Susceptibilities of Select Commercial-Off-the-Shelf Components for Space	64
<i>Daniel H. Lo and Thien C. Tran, Northrop Grumman Space Systems, One Space Park, Redondo Beach</i>	
Single Event Upset and Total Ionizing Dose Response of 12LP FinFET Digital Circuits	71
<i>Jereme Neuendank, Matthew Spear, Trace Wallace, Donald Wilson, Jose Solano, Gedeon Irumva, Ivan Sanchez Esqueda, Hugh J. Barnaby, Lawrence T. Clark, John Brunhaver, Marek Turowski, Esko Mikkola, David Hughart, Joshua Young, Jack Manuel, Sapan Agarwal, Bastiaan Vaandrager, Gyorgy Vizkelethy, Amos Gutierrez, James Trippe, Michael King, Edward Bielejec, and Matthew Marinella</i>	

SET Characterization of a High and Low Side Gate Driver (RIC7S113) using Pulsed Laser and Heavy Ion Testing.....	80
<i>Jeffrey H. Warner, Johns Hopkins Applied Physics Laboratory, Laurel; Eric Faraci, IR HiRel, an Infineon Technologies Company, 35 New England, Business Center Dr. Suite 100, Andover; Chi Pham, Johns Hopkins Applied Physics Laboratory, Laurel; Ani Khachatrian, and Dale McMorro, US Naval Research Laboratory, Washington</i>	
Neutron-Induced Single-Event Effects and Total Ionizing Dose in Embedded Radios	89
<i>Elizabeth C. Auden, and Michael P. Caffrey, Los Alamos National Laboratory, Los Alamos</i>	
SEL and SEU In-Flight Data from Memories On-Board PROBA-II Spacecraft.....	94
<i>C. Poivey, The European Space Agency, ESTEC, 2200 AG Noordwijk; R. Harboe-Sørensen, RHS Consultant, Kervelhof 46, 2215 BE Voorhout; M. Pinto, M. Poizat, The European Space Agency, ESTEC, 2200 AG Noordwijk; N. Fleurinck, Qinetiq Soace NV, B-9150, Kruibeke; K. Grürmann, DSI Aerospace technologies GmbH, D-38106, Braunschweig; and H. Schmidt, AIRBUS DS GmbH, 28199 Bremen</i>	
Total Ionizing Dose Response of Commercial 22nm FD-SOI CMOS Technology	100
<i>Jose Solano, Matthew Spear, Trace Wallace, Donald Wilson, Oliver Forman, Ivan Sanchez Esqueda, Hugh Barnaby, Aymeric Privat, Marek Turowski, and Rudolf Vonniederhausern</i>	
Debugging Xilinx Zynq-7000 SoC Processor Caches during Linux System Execution under Proton Irradiation	105
<i>M. Jaksch, J. Budroweit, and F. Stehle, German Aerospace Center, Bremen</i>	
Single Event Characterization of Power Components under Heavy Ion Irradiation	109
<i>N. Aksteiner and J. Budroweit, German Aerospace Center, Bremen</i>	
TID and SEE Evaluation on a Universal Input, 10-Output Low Impedance LVCMOS Buffer.....	113
<i>J. Budroweit and N. Aksteiner, German Aerospace Center, Bremen</i>	
NASA Goddard Space Flight Center's Recent Radiation Effects Test Results	117
<i>Alyson D. Topper, Martha V. O'Bryan, SSAI, work performed for NASA Goddard Space Flight Center; Edward P. Wilcox, Thomas A. Carstens, Jonathan D. Barth, NASA/GSFC, Code 561.4, Greenbelt; Melanie Berg, SSAI, work performed for NASA Goddard Space Flight Center; Megan C. Casey, Matthew B. Joplin, Jean-Marie Lauenstein, Michael J. Campola, NASA/GSFC, Code 561.4, Greenbelt; Donna J. Cochran, SSAI, work performed for NASA Goddard Space Flight Center; Jonathan A. Pellish, and Peter J. Majewicz, NASA/GSFC, Code 561.4, Greenbelt</i>	
Radiation Assessment of Two Automotive-Grade N-Channel MOSFETs.....	124
<i>Jesse Ward, Jayden McKoy, Msc. Student with STARLab, E1-451, University of Manitoba; Ian Jeffrey, Associate Professor with the University of Manitoba; David Ross, Senior Electrical Engineer with Magellan Aerospace; and Philip Ferguson, Associate Professor with STARLab and the NSERC / Magellan Aerospace Industrial Research Chair in Satellite Engineering, E1-451, University of Manitoba</i>	
The Aerospace Corporation's Compendium of Recent Radiation Testing Results.....	128
<i>S. C. Davis, A. D. Yarbrough, R. Koga, A. W. Wright, J. A. Shanney, K. G. Pham, C. Cao, S. Lin, The Aerospace Corporation, El Segundo; and B. Dooley, The Aerospace Corporation</i>	
Single Event Effect and Total Ionizing Dose Characterization of CAES 1.25 Gbps Repeater	136
<i>A. Turnbull, E. Serna, P. Nelson, M. Von Thun, and J. Yount</i>	

First Extensive Radiation Characterization of Double Capacitive SiO₂ Isolation Barrier Technology using TI's ISOS141-SEP as a Test Vehicle.....	141
<i>Michael Saul, Ram Gooty, Samantha Williams, Sadia Khan, and Khodor Elnashar</i>	
Radiation Evaluation of the TPS7H4010-SEP Step-Down Voltage Converter	145
<i>T. Lew, A. Marinelarena, J. Cruz-Colon, and N. Cunningham</i>	
A Heavy-Ion Single-Event Effects Test Facility at Michigan State University.....	150
<i>S. Lidia, S. Cogan, K. Fukushima, T. Gee, S.-H. Kim, G. Machicoane, T. Maruta, D. McNanney, P. Ostroumov, A. Plastun, X. Rao, S. Rodriguez, A. Yeck, and Q. Zhao, The Facility for Rare Isotope Beams, Michigan State University</i>	
Displacement Damage and Total Ionizing Dose at High and Low Dose Rate Performance of an Optocoupler	157
<i>Z. -W. Yang, The Department of Electrical and Computer Engineering, University of Saskatchewan; D. M. Hiemstra, MDA, Brampton; S. Shi, C. Jin, Z. -R. Li, and L. Chen, The Department of Electrical and Computer Engineering, University of Saskatchewan</i>	
Single Event Upset Characterization of the Intel Movidius Myriad X VPU and Google Edge TPU Accelerators using Proton Irradiation.....	162
<i>Devin P. Ramaswami, The Department of Electrical and Computer Engineering, University of Saskatchewan; David M. Hiemstra, MDA, Brampton; Zhi Wu Yang, Shutting Shi, and Li Chen, The Department of Electrical and Computer Engineering, University of Saskatchewan</i>	
Guide to the 2021 IEEE Radiation Effects Data Workshop Record	165
<i>David M. Hiemstra, MDA Space Missions, Brampton</i>	
Total Dose Performance at High Dose Rate of Isolated Switching Regulator Evaluation Kits	169
<i>D. M. Hiemstra, MDA, Brampton; S. Shi, and L. Chen, The Department of Electrical and Computer Engineering, University of Saskatchewan</i>	
Single Event Effect Measurements of Micron Technology 128Gb Single-Level NAND Flash Memory.....	172
<i>Farokh Irom and Gregory R. Allen, The Jet Propulsion Laboratory, California Institute of Technology Pasadena</i>	
Neutron Induced Displacement Damage in Commercial Power Management Integrated Circuits.....	176
<i>Gauri Koli, Arizona State University, Tempe; Elizabeth C. Auden, and Heather M. Quinn, The Los Alamos National Laboratory, Los Alamos</i>	
Combined Neutron and TID Results of the Intersil ISL70321SEH.....	179
<i>W. H. Newman, N.W. van Vonno, S.D. Turner, and L. G. Pearce, The Radiation Hardened Communications Group of Renesas Electronics America</i>	
Laser Techniques for Mitigation of Single Event Effects in a PWM Controller	183
<i>Theju Bernard, Eric Thomson, Lawrence Pearce, Tim Hoang-Lok, and Abigail Eberts</i>	
Radiation Results for Modern GaN-on-Si Power Transistors	186
<i>M. Zafrani, J. Brandt, R. Strittmatter, B. Sun, S. Zhang, and A. Lidow</i>	
Single Event Effects Characterization of Microchip Programmable Current Limiting Power Switch LX7712	190
<i>Marco Leuenberger, Russell Stevens, Nadia Rezzak, Microchip Technology, San Jose; and Dorian Johnson, Microchip Technology, Irvine</i>	

Radiation Evaluation of the DP83561-SP Radiation Hardened 10/100/1000 Ethernet PHY Transceiver with SEFI Handling Sub-System.	194
<i>R. Gooty, G. Modi, S. Williams, K. Kruckmeyer, V. Salomon, and D. Boldrin</i>	
Radiation Characterization Results of AP54RHC 30 krad(Si) Logic Family.....	197
<i>A. Ghoshal, Test Engineer with Apogee Semiconductor; A. Billings, Analog Design Engineer with Apogee Semiconductor; M. Hamlyn, A. Quiroz, and K. Schulmeyer, Member, IEEE</i>	
Accelerated Nuclear Radiation Effects on the Raspberry Pi 3B+.....	203
<i>Charles J. Corley, Graduate student at the University of Texas at Austin; Heather M. Quinn, Senior researcher at the Los Alamos National Laboratory; and Earl E. Swartzlander, Professor at the University of Texas at Austin</i>	
Raspberry Pi Zero and 3B+ SEE and TID Test Results.....	211
<i>Steven M. Guertin, Sergeh Vartanian, and Andrew C. Daniel, Jet Propulsion Laboratory, California Institute of Technology</i>	
Total Ionizing Dose and Reliability Evaluation of the ST-DDR4 Spin-Transfer Torque Magnetoresistive Random Access Memory (STT-MRAM).....	216
<i>Sergeh Vartanian, Jean Yang-Scharlotta, Gregory R. Allen, Andrew C. Daniel, Daniel Costanzo, Jet Propulsion Laboratory, California Institute of Technology; Frederick B. Mancoff, Daniel Symalla, and Andy Olsen, Everspin Technologies Inc., Chandler</i>	
Total-Ionizing-Dose Effects on Threshold Voltage Distribution of 64-Layer 3D NAND Memories.....	221
<i>Mondol Anik Kumar, Md Raquibuzzaman, Matchima Buddhanoy, Electrical and Computer Engineering Department, University of Alabama in Huntsville; Maryla Wasiolek, Khalid Hattar, Sandia National Laboratories; Timothy Boykin, and Biswajit Ray, Electrical and Computer Engineering Department, University of Alabama in Huntsville</i>	
Cumulative Index.....	226
Author index	270